TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

2SC3265

Low Frequency Power Amplifier Applications Power Switching Applications

• High DC current gain: $h_{FE(1)} = 100 \sim 320$

• Low saturation voltage: $V_{CE (sat)} = 0.4 \text{ V (max)}$ (IC = 500 mA, IB = 20 mA)

• Complementary to 2SA1298

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V _{CEO}	25	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	IC	800	mA
Base current	ΙΒ	160	mA
Collector power dissipation	PC	200	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C

Unit: mm 2.5-0.3 2.5-0.3 1.5-0.15 2.5-0.3 3. F. 0.25 4.0.25 5.0.01 5.001

2-3F1A

Weight: 0.012 g (typ.)

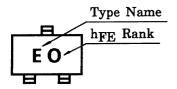
TOSHIBA

Electrical Characteristics (Ta = 25°C)

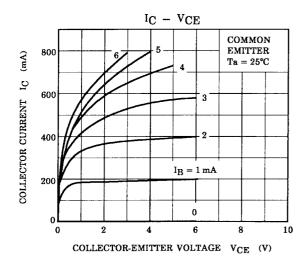
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 30 \text{ V}, I_{E} = 0$	_	_	0.1	μА
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	0.1	μА
Collector-emitter breakdown voltage	V (BR) CEO	$I_C = 10 \text{ mA}, I_B = 0$	25	_	_	V
Emitter-base breakdown voltage	V (BR) EBO	$I_E = 0.1 \text{ mA}, I_C = 0$	5	_	_	V
DC current gain	h _{FE (1)} (Note)	V _{CE} = 1 V, I _C = 100 mA	100	_	320	
	h _{FE (2)}	V _{CE} = 1 V, I _C = 800 mA	40	_	_	
Collector-emitter saturation voltage	V _{CE (sat)}	$I_C = 500 \text{ mA}, I_B = 20 \text{ mA}$	_	_	0.4	V
Base-emitter voltage	V _{BE}	V _{CE} = 1 V, I _C = 10 mA	0.5	_	0.8	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 10 mA	_	120	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz		13		pF

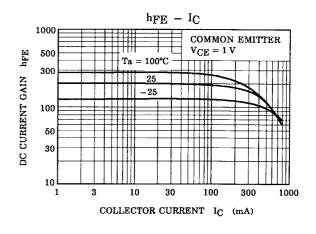
Note: hFE (1) classification O: 100~200, Y: 160~320

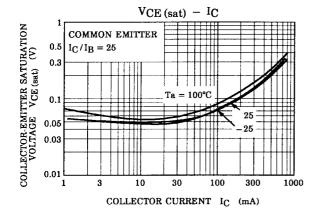
Marking

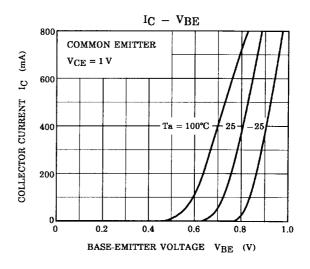


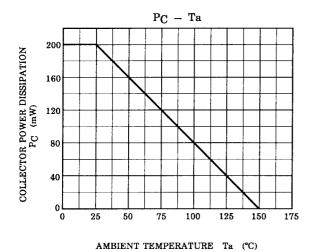
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